

AS
secondary ion mass spectroscopy is conducted on the crystalline semiconductor film to reveal that the film contains less than 5×10^{18} nitrogen atoms per cm^3 , less than 5×10^{18} carbon atoms per cm^3 , and less than 1×10^{19} oxygen atoms per cm^3 .


REMARKS

In response to the election of species in the Office Action of August 23, 2002, Applicants hereby elect without traverse embodiment 3 of Fig. 17 as provided on page 2 of the Office Action. Claims 1-52 are readable thereon.

Applicants have also amended claims 15, 22, 29, 36 and 43 to recite the invention to which Applicants are entitled.

Consideration and allowance of the instant application are now respectfully requested.

Respectfully submitted,



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Attachment to Amendment

15. A semiconductor device whose pixel portion and driver circuit are formed [on] over a same insulator, wherein:

thin film transistors in the pixel portion and in the driver circuit are all n-channel transistors;

each of the thin film transistors has a channel formation region formed of a crystalline semiconductor film that contains silicon as its main ingredient and germanium;

20% or more of the crystalline semiconductor film is the {101} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline semiconductor film, the plane being detected by an electron backscatter diffraction pattern method;

3% or less of the crystalline semiconductor film is the {001} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline semiconductor film;

5% or less of the crystalline semiconductor film is the {111} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline semiconductor film; and

secondary ion mass spectroscopy is conducted on the crystalline semiconductor film to reveal that the film contains less than 5×10^{18} nitrogen atoms per cm^3 , less than 5×10^{18} carbon atoms per cm^3 , and less than 1×10^{19} oxygen atoms per cm^3 .

22. A semiconductor device whose pixel portion and driver circuit are formed [on] over a same insulator, wherein:

thin film transistors in the pixel portion and in the driver circuit are all p-channel transistors;

each of the thin film transistors has a channel formation region formed of a crystalline semiconductor film that contains silicon as its main ingredient and germanium;

20% or more of the crystalline semiconductor film is the {101} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline

semiconductor film, the plane being detected by an electron backscatter diffraction pattern method;

3% or less of the crystalline semiconductor film is the {001} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline semiconductor film;

5% or less of the crystalline semiconductor film is the {111} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline semiconductor film; and

secondary ion mass spectroscopy is conducted on the crystalline semiconductor film to reveal that the film contains less than 5×10^{18} nitrogen atoms per cm^3 , less than 5×10^{18} carbon atoms per cm^3 , and less than 1×10^{19} oxygen atoms per cm^3 .

29. A semiconductor device whose pixel portion and driver circuit are formed [on] over a same insulator, wherein:

the driver circuit is composed of an n-channel thin film transistor and a p-channel thin film transistor;

each of the n-channel and p-channel thin film transistors has a channel formation region formed of a crystalline semiconductor film that contains silicon as its main ingredient and germanium;

20% or more of the crystalline semiconductor film is the {101} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline semiconductor film, the plane being detected by an electron backscatter diffraction pattern method;

3% or less of the crystalline semiconductor film is the {001} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline semiconductor film;

5% or less of the crystalline semiconductor film is the {111} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline semiconductor film; and

secondary ion mass spectroscopy is conducted on the crystalline semiconductor film to reveal that the film contains less than 5×10^{18} nitrogen atoms per cm^3 , less than 5×10^{18} carbon atoms per cm^3 , and less than 1×10^{19} oxygen atoms per cm^3 .

36. A semiconductor device whose pixel portion is formed [on] over an insulator, wherein:
thin film transistors in the pixel portion each have a channel formation region formed of a crystalline semiconductor film that contains silicon as its main ingredient and germanium;

20% or more of the channel formation region is the {101} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline semiconductor film, the plane being detected by an electron backscatter diffraction pattern method;

3% or less of the channel formation region is the {001} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline semiconductor film;

5% or less of the channel formation region is the {111} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline semiconductor film; and

secondary ion mass spectroscopy is conducted on the channel formation region to reveal that the region contains less than 5×10^{18} nitrogen atoms per cm^3 , less than 5×10^{18} carbon atoms per cm^3 , and less than 1×10^{19} oxygen atoms per cm^3 .

43. A semiconductor device whose pixel portion and driver circuit are formed [on] over a same insulator, wherein:

the driver circuit includes a buffer composed of thin film transistors of one type of conductivity;

the buffer has a first one conductivity thin film transistor and a second one conductivity thin film transistor, the second one conductivity thin film transistor being connected to the first one conductivity thin film transistor in series and having as its gate a drain of the first one conductivity thin film transistor;

each of the first and second thin film transistors has a channel formation region formed of a crystalline semiconductor film that contains silicon as its main ingredient and germanium;

20% or more of the crystalline semiconductor film is the {101} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline semiconductor film, the plane being detected by an electron backscatter diffraction pattern method;

3% or less of the crystalline semiconductor film is the {001} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline semiconductor film;

5% or less of the crystalline semiconductor film is the {111} lattice plane that forms an angle of equal to or less than 10 degree with respect to the surface of the crystalline semiconductor film; and

secondary ion mass spectroscopy is conducted on the crystalline semiconductor film to reveal that the film contains less than 5×10^{18} nitrogen atoms per cm^3 , less than 5×10^{18} carbon atoms per cm^3 , and less than 1×10^{19} oxygen atoms per cm^3 .